# Electronic Version v1.1 Stylesheet Version v1.1

| SUBMISSION TYPE:      | NEW ASSIGNMENT |
|-----------------------|----------------|
| NATURE OF CONVEYANCE: | ASSIGNMENT     |

## **CONVEYING PARTY DATA**

| Name            | Execution Date |
|-----------------|----------------|
| Cheng-Tung Lin  | 05/07/2008     |
| Yung-Sheng Chiu | 05/07/2008     |
| Hsiang-Yi Wang  | 05/07/2008     |
| Chia-Lin Yu     | 05/07/2008     |
| Chen-Hua Yu     | 05/07/2008     |

## **RECEIVING PARTY DATA**

| Name:           | Futurewei Technologies, Inc. |
|-----------------|------------------------------|
| Street Address: | 1700 Alma Drive              |
| City:           | Plano                        |
| State/Country:  | TEXAS                        |
| Postal Code:    | 75075                        |

## PROPERTY NUMBERS Total: 1

| Property Type       | Number   |
|---------------------|----------|
| Application Number: | 12118919 |

# **CORRESPONDENCE DATA**

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Correspondent Name: Slater & Matsil, LLP

Address Line 1: 17950 Preston Road, Suite 1000

Address Line 4: Dallas, TEXAS 75252

| ATTORNEY DOCKET NUMBER: | TSM08-0054   |
|-------------------------|--------------|
| NAME OF SUBMITTER:      | Joanna Smith |

PATENT REEL: 020935 FRAME: 0700

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PATENT REEL: 020935 FRAME: 0701

ATTORNEY DOCKET NO. TSM08-0054

#### **ASSIGNMENT**

WHEREAS, I, the undersigned inventor (or one of the undersigned joint inventors), of residence as listed, having invented certain new and useful improvements as below entitled, for which application for United States Letters Patent is made, the said application having been executed on the date set forth below; and

WHEREAS. Taiwan Semiconductor Manufacturing Company, Ltd. (TSMC), a corporation organized and existing under the laws of Taiwan, the Republic of China, with its principal office at No. 8, Li-Hsin Rd. 6, Science-Based Industrial Park, Hsin-Chu, Taiwan 300-77, R.O.C., is desirous of acquiring my entire right, title and interest in and to the said invention, and to the said application and any Letters Patent that may issue thereon in the United States and all other countries throughout the world;

NOW, THEREFORE, for good and valuable consideration, the receipt of which is hereby acknowledged, I hereby sell and assign to the said TSMC, its successors and assigns, my entire right, title and interest in and to the said invention and in to the said application and all patents which may be granted therefor, and all divisions, reissues, substitutions, continuations, and extensions thereof; and I hereby authorize and request the Commissioner for Patents to issue all patents for said invention, or patent resulting therefrom, insofar as my interest is concerned, to the said TSMC, as assignee of my entire right, title and interest. I declare that I have not executed and will not execute any agreement in conflict herewith.

! also hereby sell and assign to TSMC, its successors and assigns, my foreign rights to the invention disclosed in said application, in all countries of the world, including, but not limited to, the right to file applications and obtain patents under the terms of the International Convention for the Protection of Industrial Property, and of the European Patent Convention, and further agree to execute any and all patent applications, assignments, affidavits, and any other papers in connection therewith necessary to perfect such patent rights.

I hereby further agree that I will communicate to said TSMC, or to its successors, assigns, and legal representatives, any facts known to me respecting said invention or the file history thereof, and at the expense of said assignee company, testify in any legal proceedings, sign all lawful papers, execute all divisional, continuation, reissue and substitute applications, make all lawful oaths, and generally do everything possible to aid said TSMC, its successors, assigns and nominees to obtain and enforce proper patent protection for said invention in all countries.

IN WITNESS WHEREOF, I hereunto set my hand and seal this day and year;

| TITLE<br>OF<br>INVENTION                | MOSFET                      | S Having Stacked M                   | letal Gate Electrodes            | and Method     |
|---|-----------------------------|--------------------------------------|----------------------------------|----------------|
| SIGNATURE<br>OF<br>INVENTOR<br>AND NAME | Charg-Ting Lin              | Afring Sheng Chin<br>Yung-Sheng Chiu | Hsiang-Yi Wang<br>Hsiang-Yi Wang | Chia-Lin Yu    |
| DATE                                    | 8000/10/10                  | 05/07/2008                           | 65/07/2008                       | 05/07/2008     |
| RESIDENCE<br>(City, County,<br>State)   | Jhudong Township,<br>Taiwan | Hsin-Chu, Taiwan                     | Hsin-Chu, Taiwan                 | Sigang, Taiwan |

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Assignment

PATENT REEL: 020935 FRAME: 0702 7-11-4 300#/05/67 10:30:NE

| ATTORNEY DOCKET | NO. |
|-----------------|-----|
| TSM08-0054      |     |

#### ASSIGNMENT

WHEREAS, I, the undersigned inventor (or one of the undersigned joint inventors), of residence as listed, having invented certain new and useful improvements as below entitled, for which application for United States Letters Patent is made, the said application having been executed on the date set forth below; and

WHEREAS, Taiwan Semiconductor Manufacturing Company, Ltd. (TSMC), a corporation organized and existing under the laws of Taiwan, the Republic of China, with its principal office at No. 8, Li-Hsin Rd. 6, Science-Based Industrial Park, Hsin-Chu, Taiwan 300-77, R.O.C., is desirous of acquiring my entire right, title and interest in and to the said invention, and to the said application and any Letters Patent that may issue thereon in the United States and all other countries throughout the world;

NOW, THEREFORE, for good and valuable consideration, the receipt of which is hereby acknowledged, I hereby sell and assign to the said TSMC, its successors and assigns, my entire right, title and interest in and to the said invention and in to the said application and all patents which may be granted therefor, and all divisions, reissues, substitutions, continuations, and extensions thereof; and I hereby authorize and request the Commissioner for Patents to issue all patents for said invention, or patent resulting therefrom, insofar as my interest is concerned, to the said TSMC, as assignee of my entire right, title and interest. I declare that I have not executed and will not execute any agreement in conflict herewith.

I also hereby sell and assign to TSMC, its successors and assigns, my foreign rights to the invention disclosed in said application, in all countries of the world, including, but not limited to, the right to file applications and obtain patents under the terms of the International Convention for the Protection of Industrial Property, and of the European Patent Convention, and further agree to execute any and all patent applications, assignments, affidavits, and any other papers in connection therewith necessary to perfect such patent rights.

I hereby further agree that I will communicate to said TSMC, or to its successors, assigns, and legal representatives, any facts known to me respecting said invention or the file history thereof, and at the expense of said assignee company, testify in any legal proceedings, sign all lawful papers, execute all divisional, continuation, reissue and substitute applications, make all lawful oaths, and generally do everything possible to aid said TSMC, its successors, assigns and nominees to obtain and enforce proper patent protection for said invention in all countries.

IN WITNESS WHEREOF, I hereunto set my hand and seal this day and year;

| TITLE<br>OF<br>INVENTION                | ethod and Tool Concept to Make a Metal Gate Stack with Minimized Plasma<br>Damage and Interfacial Layer Regrowth |  |
|---|--|--|
| SIGNATURE<br>OF<br>INVENTOR<br>AND NAME | Chen-Hua Yu  |  |
| DATE                                    | 5/7/08   |  |
| RESIDENCE<br>(City, County,<br>State)   | Hsin-Chu, Taiwan   |  |

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Assignment

PATENT TOTAL P.05

RECORDED: 05/12/2008 REEL: 020935 FRAME: 0703